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Preliminary KA5L0380R

SPS

The SPS product family is specially designed for an off-line SMPS with minimal external components. The SPS consist of high voltage power SenseFET and current mode PWM IC.

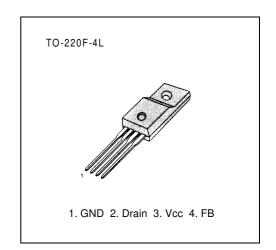
Included PWM controller features integrated fixed frequency oscillator, under voltage lock-out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shutdown protection, over voltage protection, and temperature compensated precision current sources for loop compensation and fault protection circuitry. Compared to discrete MOSFET and PWM controller or RCC solution, a SPS can reduce total component count, design size, weight and at the same time increase efficiency, productivity, and system reliability.

It has a basic platform well suited for cost-effective design in either a flyback converter or a forward converter.

FEATURES

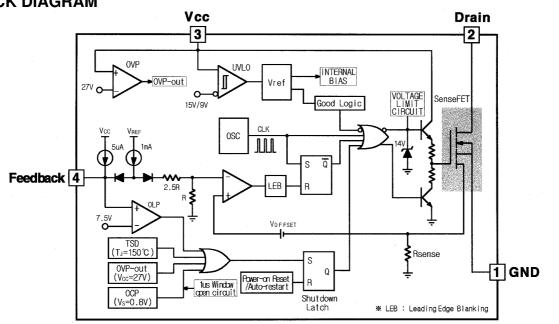
- Precision fixed operating frequency (50kHz)
- Low start-up current (Typ. 100mA)
- Pulse by pulse current limiting
- Over current protection
- Over voltage protection (Min. 25V)
- · Internal thermal shutdown function
- Under voltage lockout
- Internal high voltage sense FET
- Auto-restart mode

BLOCK DIAGRAM



ORDERING INFORMATION

Device	Package	Topr (°C)
KA5L0380R	TO-220F-4L	–25°C to +85°C



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Publication Order Number: KA5L0380R/D

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Drain-source (GND) voltage ⁽¹⁾	V _{DSS}	800	V
Drain-Gate voltage (R_{GS} =1M Ω)	V _{DGR}	800	V
Gate-source (GND) voltage	V _{GS}	±30	V
Drain current pulsed ⁽²⁾	I _{DM}	12	A _{DC}
Single pulsed avalanche energy $^{(3)}$	E _{AS}	95	mJ
Avalanche current ⁽⁴⁾	I _{AS}	-	А
Continuous drain current (T _C =25°C)	I _D	3.0	A _{DC}
Continuous drain current (T _C =100°C)	I _D	2.1	A _{DC}
Supply voltage	V _{CC}	30	V
Analog input voltage range	V _{FB}	–0.3 to V _{SD}	V
Total power dissipation	P _D (wt H/S)	35	W
	Derating	0.28	W/°C
Operating temperature	T _{OPR}	-25 to +85	٥C
Storage temperature	T _{STG}	-55 to +150	٥C

NOTES:

1. Tj=25°C to 150°C

Repetitive rating: Pulse width limited by maximum junction temperature
L=51mH, starting Tj=25°C
L=13uH, starting Tj=25°C

ELECTRICAL CHARACTERISTICS (SFET part)

(Ta=25°C unless otherwise specified)

Characteristic	Symbol	Test condition	Min.	Тур.	Max.	Unit
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =50µA	800	_	_	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =Max., Rating, V _{GS} =0V	_	_	250	μA
		V_{DS} =0.8Max., Rating, V_{GS} =0V, T _C =125°C	_	_	1000	μA
Static drain-source on resistance (note)	R _{DS(ON)}	V _{GS} =10V, I _D =0.5A	_	4	5	Ω
Forward transconductance (note)	gfs	V _{DS} =50V, I _D =0.5A	1.5	2.5	-	S
Input capacitance	Ciss	V _{GS} =0V, V _{DS} =25V, f=1MHz	_	779	_	pF
Output capacitance	Coss		_	75.6	_	
Reverse transfer capacitance	Crss		_	24.9	_	
Turn on delay time	td(on)	V_{DD} =0.5B V_{DSS} , I_D =1.0A (MOSFET switching time are essentially independent of operating temperature)	_	40	_	nS
Rise time	tr		_	95	_	
Turn off delay time	td(off)		_	150	_	
Fall time	tf		_	60	_	
Total gate charge (gate-source+gate-drain)	Qg	V_{GS} =10V, I_D =1.0A, V_{DS} =0.5B V_{DSS} (MOSFET switching time are essentially independent of operating temperature)	_	-	34	nC
Gate-source charge	Qgs		_	7.2	_	
Gate-drain (Miller) charge	Qgd		_	12.1	_	

NOTE: Pulse test: Pulse width $\leq 300\mu S$, duty cycle $\leq 2\%$

ELECTRICAL CHARACTERISTICS (Control part)

(Ta=25°C unless otherwise specified)

Characteristic	Symbol	Test condition	Min.	Тур.	Max.	Unit
REFERENCE SECTION						
Output voltage ⁽¹⁾	Vref	Ta=25°C	4.80	5.00	5.20	V
Temperature Stability (1)(2)	Vref/∆T	–25°C≤Ta≤+85°C	_	0.3	0.6	mV/°C
OSCILLATOR SECTION				1		
Initial accuracy	F _{OSC}	Ta=25°C	45	50	55	kHz
Frequency change with temperature ⁽²⁾	$\Delta F / \Delta T$	–25°C≤Ta≤+85°C	-	±5	±10	%
PWM SECTION				1		
Maximum duty cycle	Dmax	_	74	77	80	%
FEEDBACK SECTION				1		
Feedback source current	I _{FB}	Ta=25°C, 0V <u><</u> Vfb <u>≤</u> 3V	0.7	0.9	1.1	mA
Shutdown delay current	Idelay	Ta=25°C, 5V≤Vfb≤V _{SD}	4	5	6	μA
OVER CURRENT PROTECTION SECT	ION	•	1			
Over current protection	I _L (max)	Max. inductor current	1.89	2.15	2.41	А
UVLO SECTION		•	1			
Start threshold voltage	Vth(H)	-	8.4	9	9.6	V
Minimum operating voltage	Vth(L)	After turn on	14	15	16	V
TOTAL STANDBY CURRENT SECTIO	N	•	1			
Start current	I _{ST}	V _{CC} =14V	-	0.1	0.17	mA
Operating supply current (control part only)	I _{OPR}	V _{CC} ≤28	-	7	12	mA
SHUTDOWN SECTION			1	1	1	1
Shutdown Feedback voltage	V _{SD}	Vfb <u>≥</u> 6.5V	6.9	7.5	8.1	V
Thermal shutdown temperature (Tj) $^{(1)}$	T _{SD}	_	140	160	_	°C
Over voltage protection	V _{OVP}	V _{CC} ≥24V	25	27	29	V

NOTES:

1. These parameters, although guaranteed, are not 100% tested in production

2. These parameters, although guaranteed, are tested in EDS (wafer test) process

TYPICAL PERFORMANCE CHARACTERISTICS (SFET part)

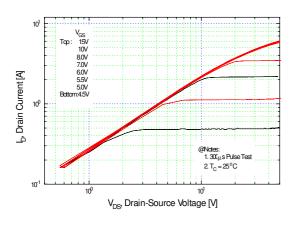
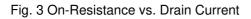


Fig 1. Output Characteristics



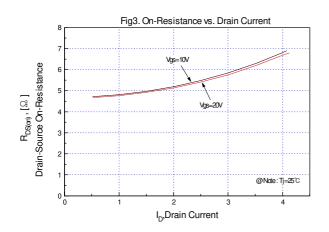
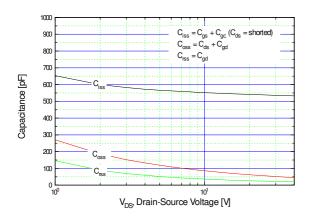


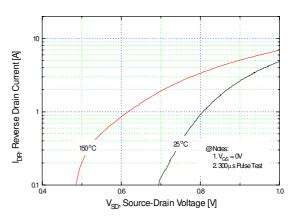
Fig.5 Capacitance vs. Drain-Source Voltage

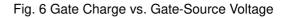


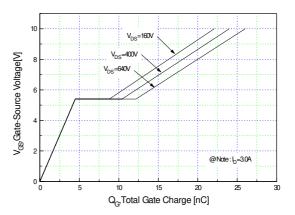
10¹ l_D, Drain Current [A] 10⁰ 150°C @Notes: 1. V_{DS} = 30 V 2. 300 μ s Puise Test 25°C -25°C 10⁻¹ 10 V_{GS'} Gate-Source Voltage [V]

Fig. 2 Transfer Characteristics

Fig. 4 Source-Drain Diode Forward Voltage







5

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

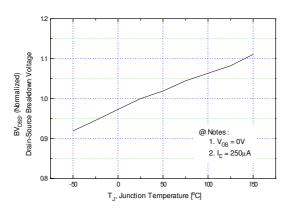


Fig. 7 Breakdown Voltage vs. Temperature

Fig. 9 Max. Safe Operating Area

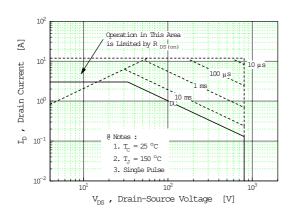


Fig. 11 Thermal Response

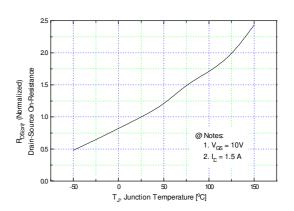
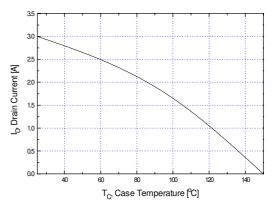
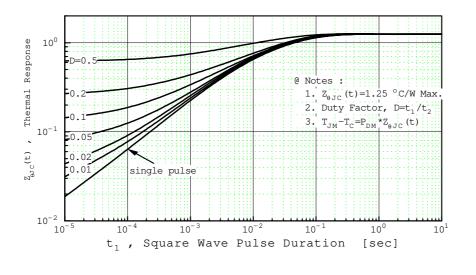


Fig. 8 On-Resistance vs. Temperature

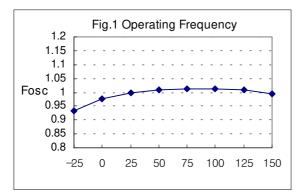
Fig. 10 Max. Drain Current vs. Case Temperature

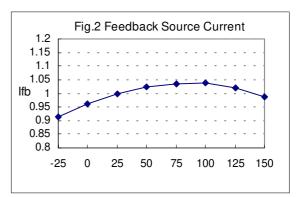


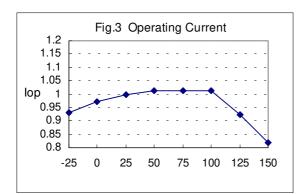


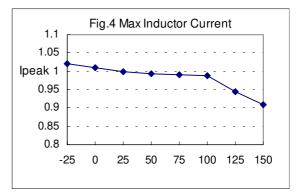
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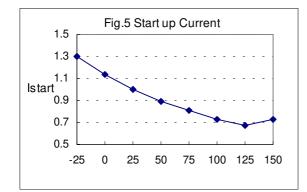
TYPICAL PERFORMANCE CHARACTERISTICS (Control part)

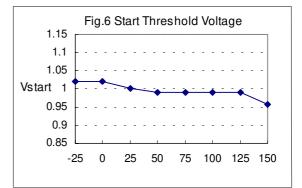






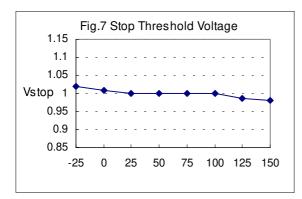


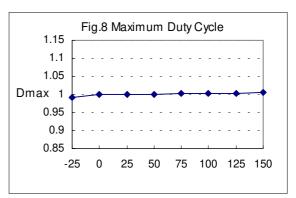


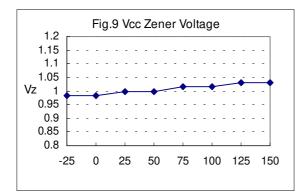


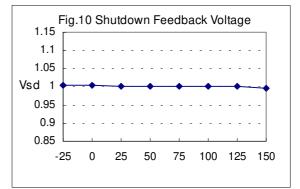
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

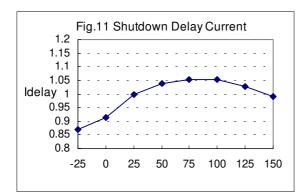
(These characteristic graphs are normalized at Ta=25°C)

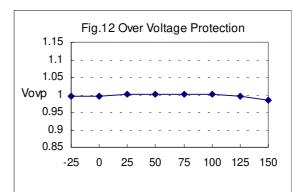








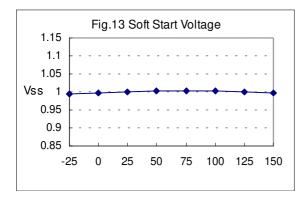


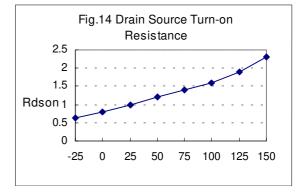




TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(These characteristic graphs are normalized at Ta=25°C)





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